

Amendments to the Claims

1. *(Previously Presented)* Semiconductor device comprising a substrate with a multilayer structure, the multilayer structure including a quantum well structure having a semiconductor layer sandwiched by further layers of an electrical insulating material.
2. *(Previously Presented)* Semiconductor device as claimed in claim 1, characterized in that one or more multilayer substructures each comprising a further semiconductor layer and a further electrical insulator layer are stacked on the quantum well structure forming a superlattice.
3. *(Currently Amended)* Semiconductor device as claimed in claim 2, characterized in that the insulator is a high-k material having a larger dielectric constant than that of SiO₂.
4. *(Original)* Semiconductor device as claimed in claim 3, characterized in that the high-k material is crystalline.
5. *(Previously Presented)* Semiconductor device as claimed in claim 4, characterized in that there is epitaxy between the high-k material and the semiconductor material of the semiconductor layer.
6. *(Previously Presented)* Semiconductor device as claimed in claim 1, characterized in that the semiconductor device is a field effect transistor with a gate, the gate being positioned substantially parallel to the at least one quantum well structure.
7. *(Previously Presented)* Semiconductor device as claimed in claim 6, characterized in that the at least one quantum well and the further quantum well have a distance whereby the at least one quantum well functions as a gate for the further quantum well.
8. *(Previously Presented)* Semiconductor device as claimed in claim 1, characterized in that the insulating layer has an equivalent silicon oxide thickness of less than 1 nm.

9. *(Previously Presented)* Semiconductor device-as claimed in claim 1, characterized in that the semiconductor layer comprises silicon.

10. *(Previously Presented)* Semiconductor device as claimed in claim 9, characterized in that the thickness of the semiconductor layer is less than 10 nm.

11. *(Previously Presented)* Semiconductor device as claimed in claim 1, characterized in that the semiconductor layer is enclosed by high-k materials with different dielectric constants.

12. *(Previously Presented)* Semiconductor device as claimed in claim 7, characterized in that doped regions extending through the quantum well structures form electrical contacts to the quantum well structures.

13. *(Previously Presented)* Semiconductor device as claimed in claim 7, characterized in that there is opposite to the gate a further gate present, which further gate is separated from the gate by the quantum well structures.

Claims 14-22 *(Cancelled)*